ABSTRACT OF THE DISCLOSURE

In one aspect, the invention encompasses a semiconductor processing method. A layer of material is formed over a semiconductive wafer substrate. Some portions of the layer are exposed to energy while other portions are not exposed. The exposure to energy alters physical properties of the exposed portions relative to the unexposed portions. After the portions are exposed, the exposed and unexposed portions of the layer are subjected to common conditions. The common conditions are effective to remove the material and comprise a rate of removal that is influenced by the altered physical properties of the layer. The common conditions remove either the exposed or unexposed portions faster than the other of the exposed and unexposed portions. After the selective removal of the exposed or unexposed portions, and while the other of the exposed and unexposed portions remains over the substrate, the wafer is cut into separated die. In another aspect, the invention encompasses another semiconductor processing method. A layer of $(CH_3)_ySi(OH)_{4-y}$ is formed over a substrate. Some portions of the layer are exposed to ultraviolet light while other portions are not exposed. The exposure to ultraviolet light converts the exposed portions to $(CH_3)_xSiO_{2-x}$. After the exposure to ultraviolet light, the exposed and unexposed portions of the layer are subjected to hydrofluoric acid to selectively remove the $(CH_3)_ySi(OH)_{4-y}$ of the unexposed portions relative to the $(CH_3)_xSiO_{2-x}$ of the exposed portions.